

N-Channel Super Junction Power MOSFET IV

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

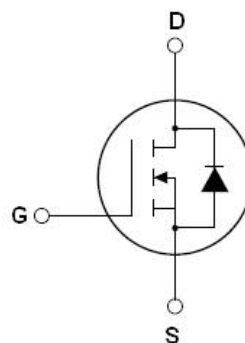
Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

$V_{DS\ min@T_{jmax}}$	710	V
$R_{DS(ON)TYP}$	160	mΩ
I_D	20	A
Q_g	28.5	nC



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE65N180T	TO-247-3L	NCE65N180T



TO-247-3L

Table 1. Absolute Maximum Ratings ($T_c=25^{\circ}C$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650	V
Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1\ Hz$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$) DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^{\circ}C$	$I_D (DC)$	20	A
Continuous Drain Current at $T_c=100^{\circ}C$	$I_D (DC)$	14	A
Pulsed drain current (Note 1)	$I_{DM} (pluse)$	60	A
Maximum Power Dissipation ($T_c=25^{\circ}C$)	P_D	194	W
Derate above $25^{\circ}C$		1.29	W/ $^{\circ}C$
Avalanche current (Note 1)	I_{AS}	6	A
Drain Source voltage slope, $V_{DS} \leq 480\ V$,	dv/dt	50	V/ns
Reverse diode dv/dt , $V_{DS} \leq 480\ V, I_{SD} \leq I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	$-55...+175$	$^{\circ}C$

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.77	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =650V, V _{GS} =0V			100	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	3	3.5	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A		160	180	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz		1550	1950	pF
Output Capacitance	C _{oss}			60		pF
Reverse Transfer Capacitance	C _{rss}			5		pF
Total Gate Charge	Q _g	V _{DS} =480V, I _D =10.5A, V _{GS} =10V		28.5		nC
Gate-Source Charge	Q _{gs}			11.7		nC
Gate-Drain Charge	Q _{gd}			5		nC
Gate plateau voltage	V _{gp}			5.7		V
Intrinsic gate resistance	R _G	f = 1 MHz open drain		2		Ω
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V, I _D =10A, R _G =1.7Ω, V _{GS} =10V		32		nS
Turn-on Rise Time	t _r			18		nS
Turn-Off Delay Time	t _{d(off)}			90		nS
Turn-Off Fall Time	t _f			8		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			20	A
Pulsed Source-drain current(Body Diode)	I _{SDM}				60	A
Forward On Voltage	V _{SD}	T _J =25℃, I _{SD} =20A, V _{GS} =0V		0.9	1.2	V
Reverse Recovery Time	t _{rr}	T _J =25℃, I _F =10A, di/dt=100A/μs		300		nS
Reverse Recovery Charge	Q _{rr}			4.5		uC
Peak Reverse Recovery Current	I _{rrm}			30		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

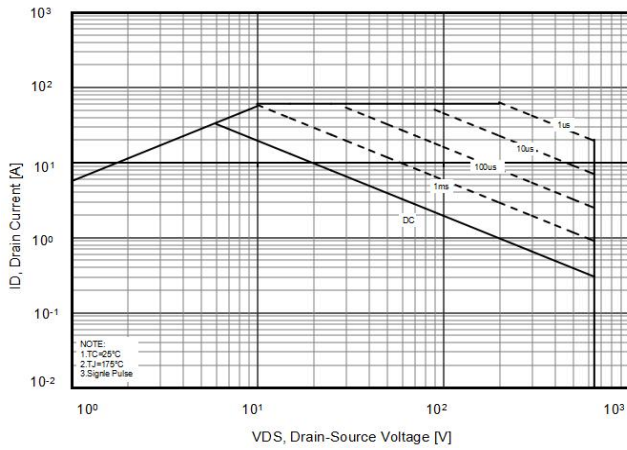


Figure2. Capacitance

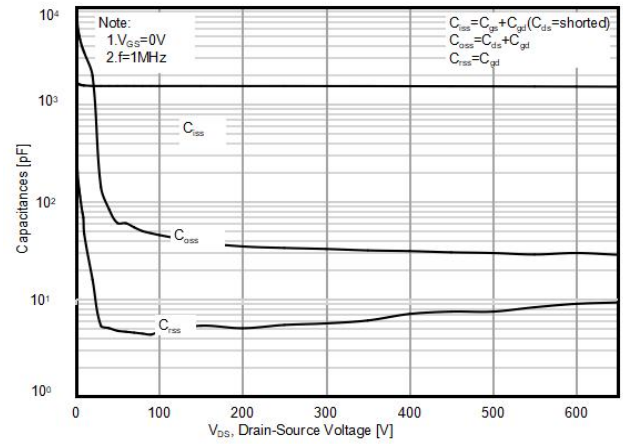


Figure3. Transfer characteristics

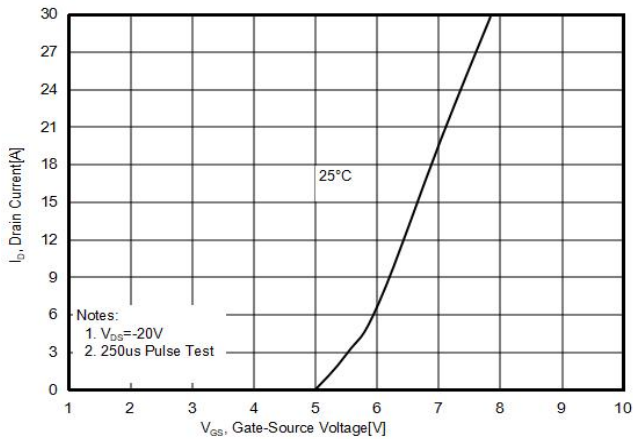


Figure4. Output characteristics

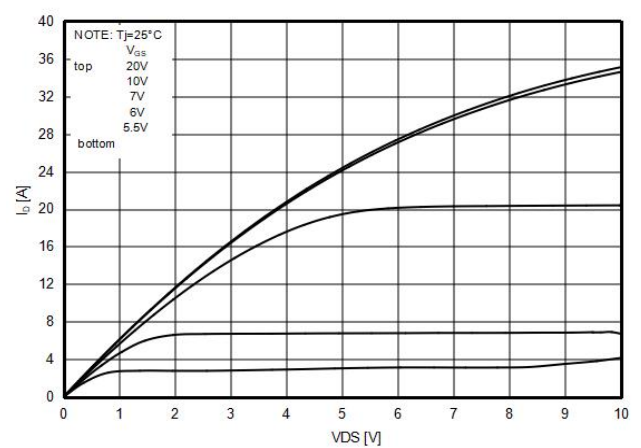


Figure5. RDS(ON) vs Junction Temperature

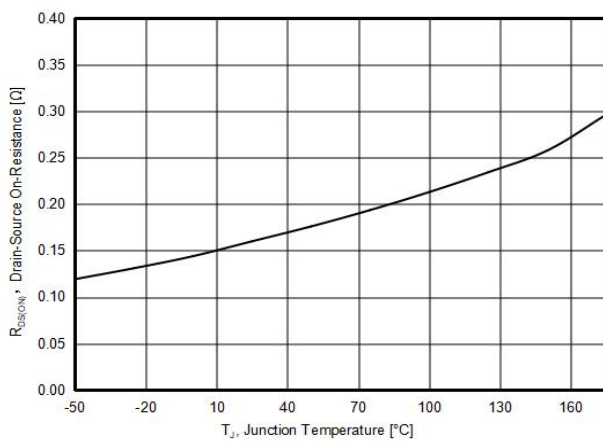


Figure6. BVDS vs Junction Temperature

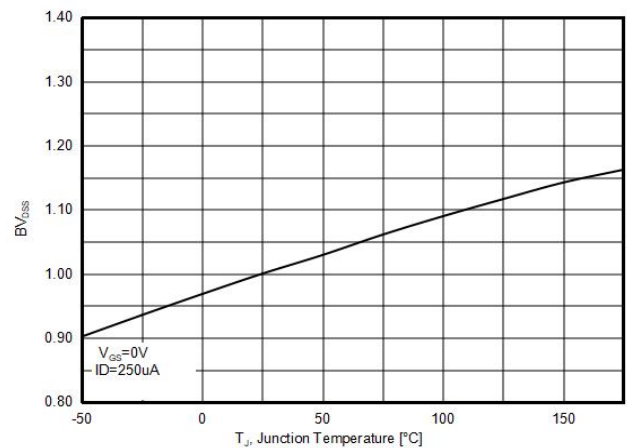


Figure7. Maximum I_D vs Junction Temperature

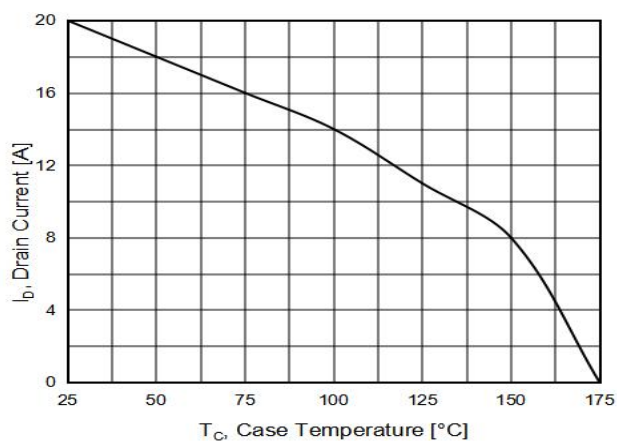


Figure8. Gate charge waveforms

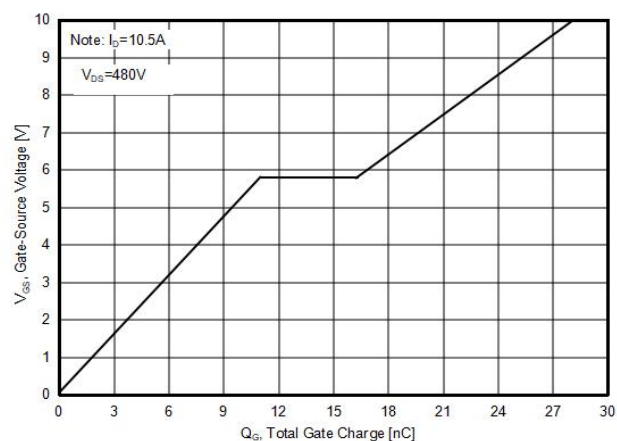


Figure9. Static drain-source on resistance

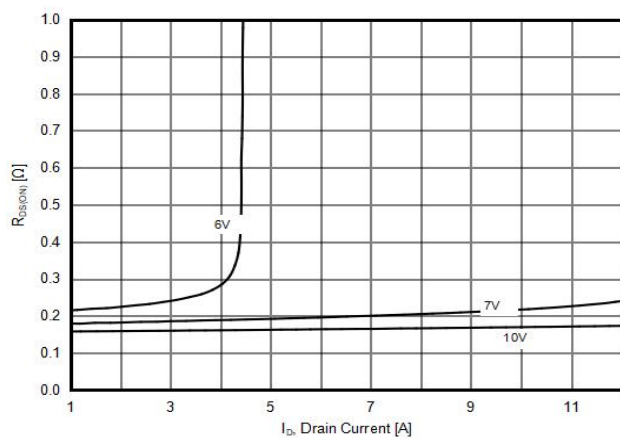
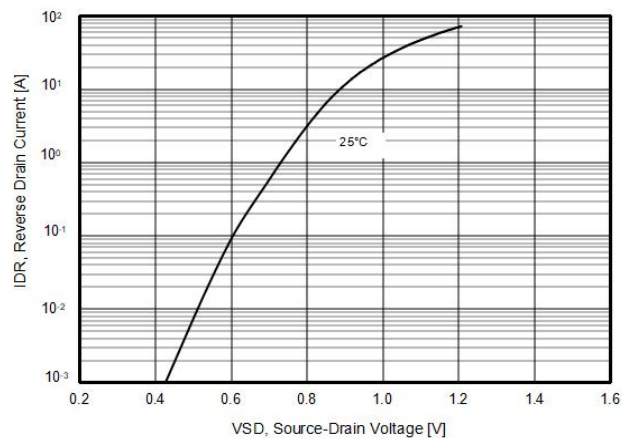
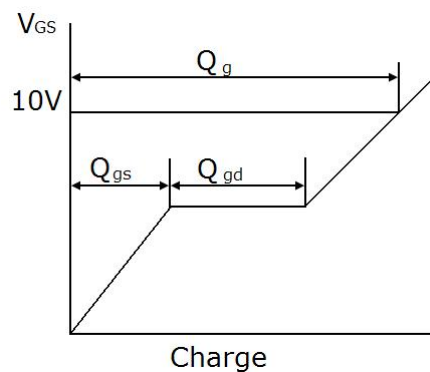
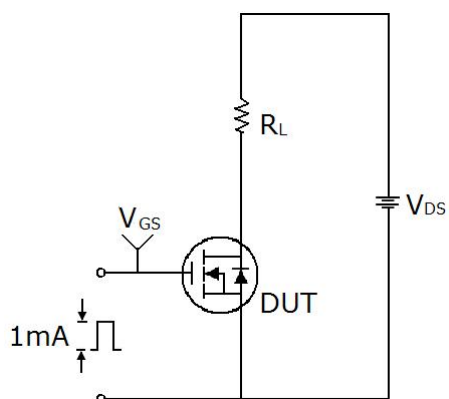


Figure10. Source-Drain Diode Forward Voltage

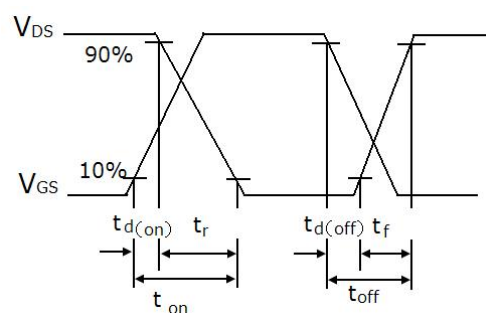
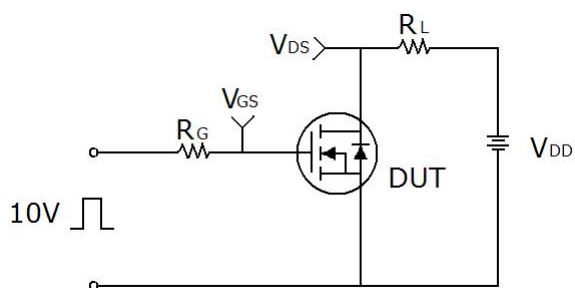


Test circuit

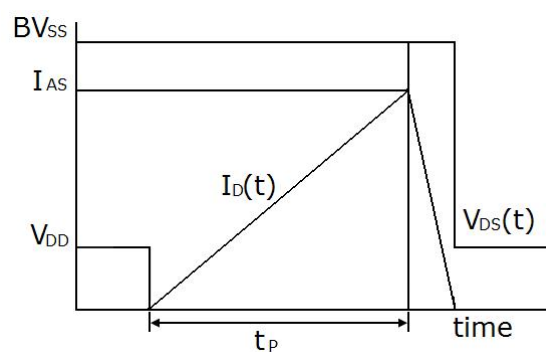
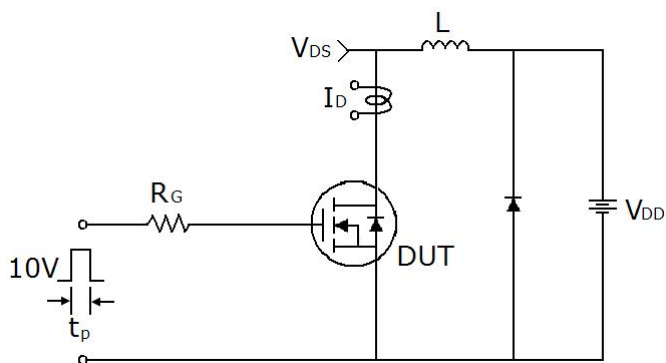
1) Gate charge test circuit & Waveform



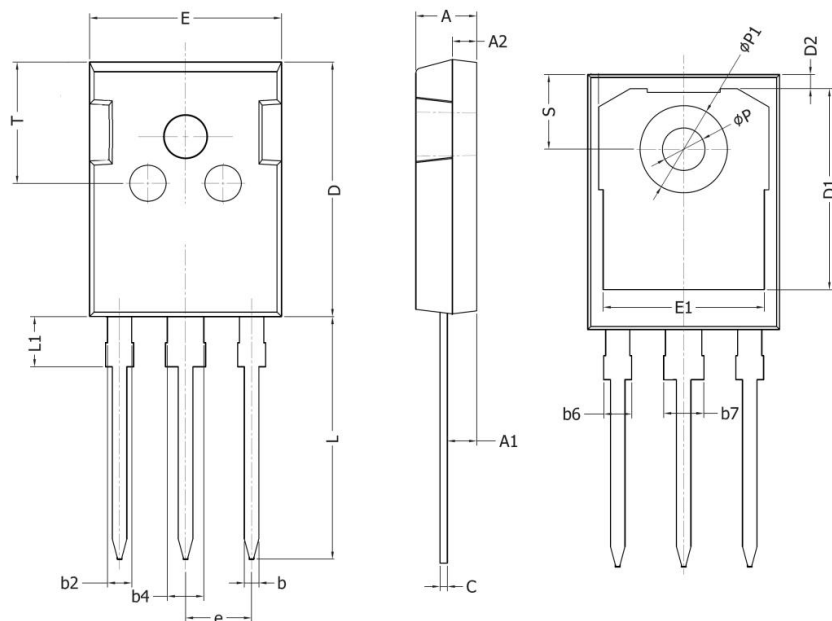
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

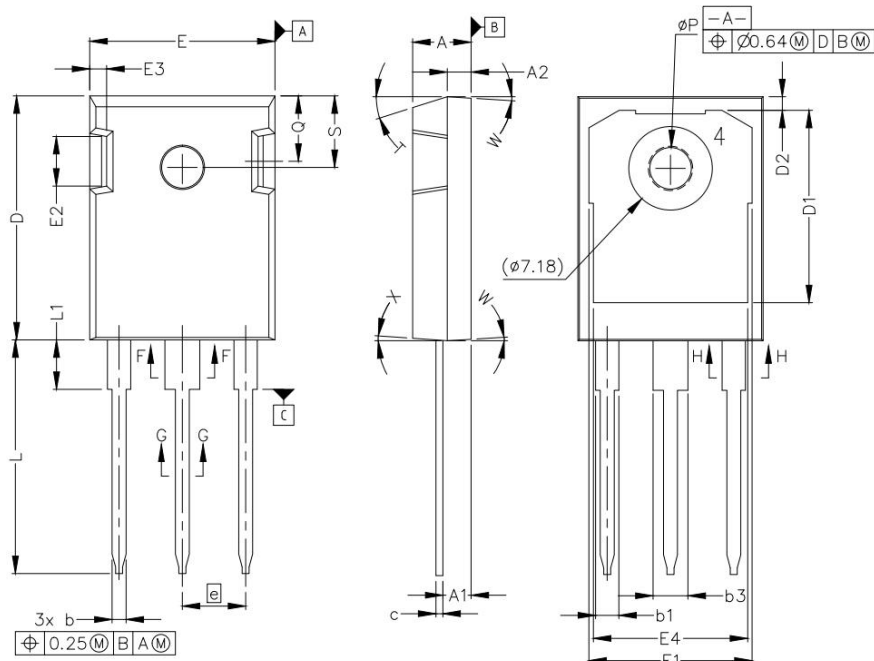


TO-247 (P) Package Information



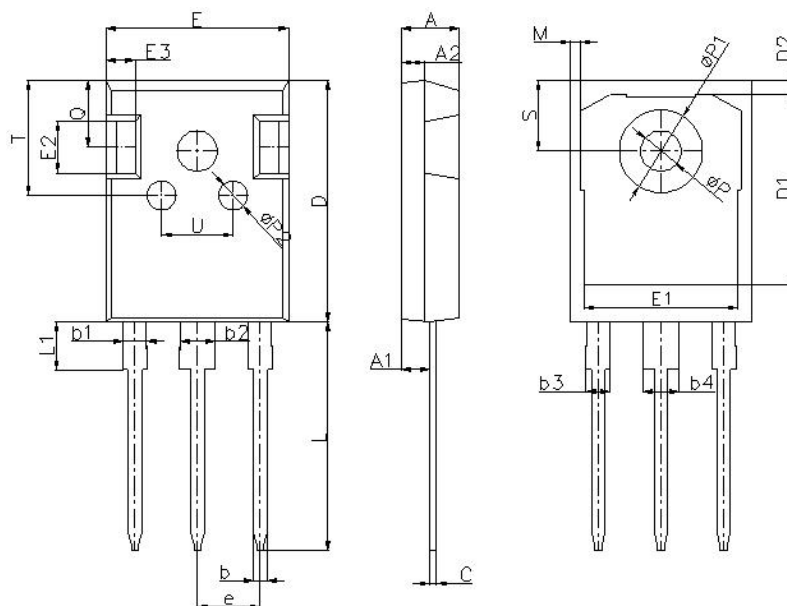
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b2	1.96	2.06	0.077	0.081
b4	2.96	3.06	0.117	0.120
b6	-	2.25	-	0.089
b7	-	3.25	-	0.128
C	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
e	5.436 BSC		0.214 BSC	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
P	3.40	3.60	0.134	0.142
P1	7.00	7.40	0.276	0.291
S	6.05	6.25	0.238	0.246
T	9.80	10.20	0.386	0.402

TO-247-B Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.07	1.33	0.042	0.052
b1	1.91	2.41	0.075	0.095
b3	2.87	3.38	0.113	0.133
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.25	0.037	0.049
E	15.75	16.13	0.620	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	1.90	0.039	0.075
E4	12.38	13.43	0.487	0.529
e	5.44 BSC		0.214 BSC	
N	3.00		0.118	
L	19.81	20.32	0.780	0.800
L1	4.10	4.40	0.161	0.173
P	3.51	3.65	0.138	0.144
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

TO-247-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.06	0.077	0.081
b2	2.96	3.06	0.117	0.120
b3	-	2.25	-	0.089
b4	-	3.25	-	0.128
C	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
E2	4.40	4.60	0.173	0.181
E3	2.40	2.60	0.094	0.102
e	5.436BSC		0.214BSC	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
M	0.35	0.95	0.014	0.037
Q	5.60	6.00	0.220	0.236
S	6.05	6.25	0.238	0.246
T	9.80	10.20	0.386	0.402
U	6.00	6.40	0.236	0.252

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